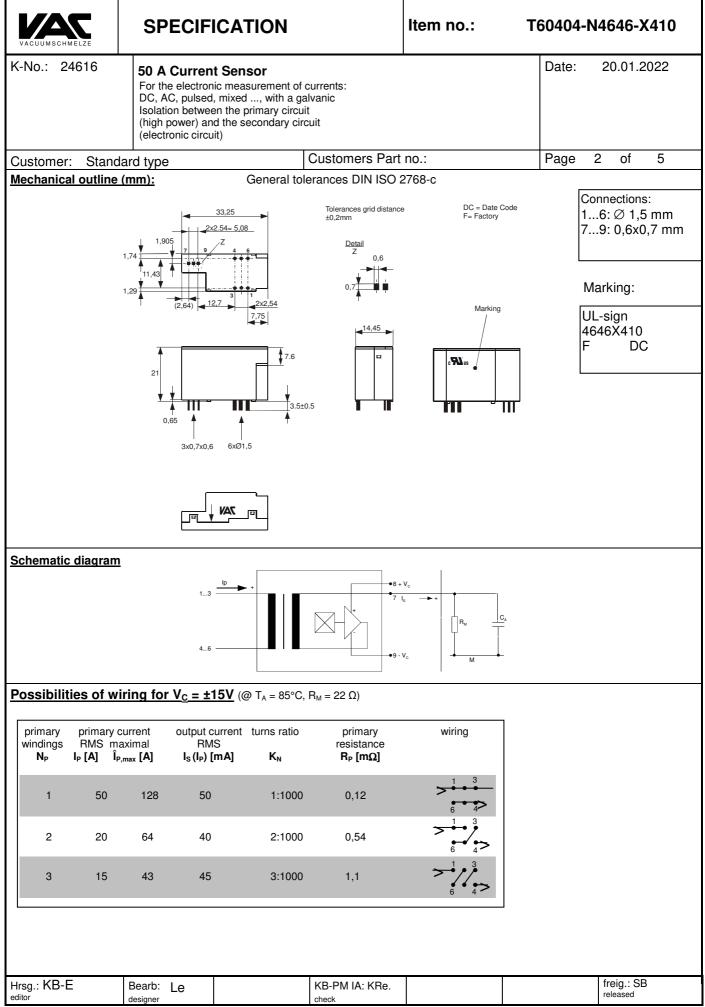
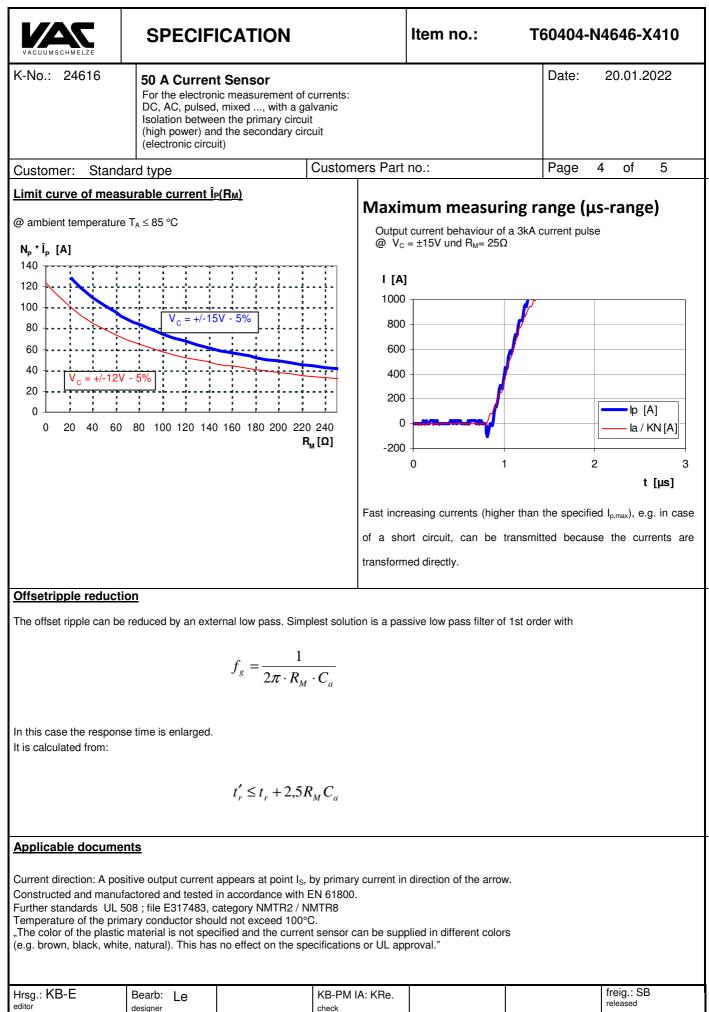
VACUUMSCHMELZE	SPECIFICATION	Item no.:	T60404-N4646-X410
C-No.: 24616	50 A Current Sensor For the electronic measurement of currents: DC, AC, pulsed, mixed, with a galvanic Isolation between the primary circuit (high power) and the secondary circuit (electronic circuit)		Date: 20.01.2022
Customer: Stan	dard type Custor	ners Part no.:	Page 1 of 5
Closed loop (comp Current Sensor with field probe	ensation) h magnetic • Very low offset current • Very low temperature depen	applications: dency and offset • AC variable	stationary operation in industrial
Printed circuit board Casing and materia		 Battery sup Switched M Power Sup 	erters for DC motor drives oplied applications Node Power Supplies (SMPS) plies for welding applications table Power Supplies (UPS)
lectrical data – R			
IPN	Primary nominal r.m.s. current		50 A
RM	Measuring resistance $V_{C}=\pm 12V$		10 200 Ω
	V _c =± 15V		22 400 Ω
I _{SN} K _N	Secondary nominal r.m.s. current Turns ratio		50 mA 13 : 1000
			13 : 1000
<u>ccuracy – Dynam</u>	nic performance data ¹⁾	min. typ.	max. Unit
I _{P,max}	Max. measuring range		
,	@ $V_{C} = \pm 12V$, $R_{M} = 10 \Omega$ ($t_{max} = 10$ sec)	±112	А
	@ $V_{C} = \pm 15V$, $R_{M} = 22 \Omega$ ($t_{max} = 10sec$)	±128	А
Х	Accuracy @ I _{PN} , T _A = 25°C	0.1	0.5 %
EL	Linearity		0.1 %
lo	Offset current @ I _P =0, T _A = 25°C	0.02	0.1 mA
tr	Response time	500	ns
• · · · ·			20
Δt (I _{P,max})	Delay time at di/dt = 100 A/µs	200	ns
f	Frequency bandwidth	200 DC200	kHz
∆t (I _{P,max}) f General data ¹⁾		DC200	kHz
f General data ¹⁾	Frequency bandwidth	5.0	-
f General data ¹⁾ T _A	Frequency bandwidth Ambient operating temperature	DC200 min. typ.	kHz <mark>max. Unit</mark> +85 °C
f General data ¹⁾ T _A T _S	Frequency bandwidth	DC200 <mark>min. typ.</mark> -40	kHz <mark>max. Unit</mark> +85 °C
f General data ¹⁾ T _A T _S m	Frequency bandwidth Ambient operating temperature Ambient storage temperature	DC200 min. typ. -40 -40 13.5	kHz <u>max. Unit</u> +85 °C +90 °C
f General data ¹⁾ T _A T _S	Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass	DC200 min. typ. -40 -40 13.5	kHz <u>max. Unit</u> +85 °C +90 °C g
f Seneral data¹⁾ T_A T_S M V_C	 Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage Current consumption Constructed and manufactored and tested 	DC200 min. typ. -40 -40 13.5 ±11.4 ±12 or ± 18,5 ed in accordance with EN 61800-	kHz max. Unit +85 °C +90 °C g 15 ±15.75 V mA
f <u>General data</u> 1) T _A T _S m V _C I _C	Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage Current consumption Constructed and manufactored and teste Reinforced insulation, Insulation materia	DC200 min. typ. -40 -40 13.5 ±11.4 ±12 or ± 18,5 ed in accordance with EN 61800- I group 1, Pollution degree 2	kHz <u>max. Unit</u> +85 °C +90 °C g 15 ±15.75 V mA 5-1 (Pin 1 - 6 to Pin 7 – 9)
f General data ¹⁾ T _A T _S m V _C I _C Sclear	Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage Current consumption Constructed and manufactored and teste Reinforced insulation, Insulation materia clearance (component without solder pad)	DC200 min. typ. -40 -40 13.5 ±11.4 ±12 or ± 18,5 ed in accordance with EN 61800- I group 1, Pollution degree 2 10.2	kHz <u>max. Unit</u> +85 °C +90 °C g 15 ±15.75 V mA 5-1 (Pin 1 - 6 to Pin 7 – 9) mm
f <u>General data</u> ¹⁾ T _A T _S m V _C I _C Sclear Screep	Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage Current consumption Constructed and manufactored and teste Reinforced insulation, Insulation materia	DC200 min. typ. -40 -40 13.5 ±11.4 ±12 or ± 18,5 ed in accordance with EN 61800- I group 1, Pollution degree 2	kHz <u>max. Unit</u> +85 °C +90 °C g 15 ±15.75 V mA 5-1 (Pin 1 - 6 to Pin 7 – 9)
f General data ¹⁾ T _A T _S m V _C I _C Sclear	Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage Current consumption Constructed and manufactored and teste Reinforced insulation, Insulation materia clearance (component without solder pad) creepage (component without solder pad) System voltage voervoltage category 3 Working voltage (table 7 acc. to EN61	DC200 min. typ. -40 -40 -40 13.5 ±11.4 ±12 or ± 18,5 ed in accordance with EN 61800- I group 1, Pollution degree 2 10.2 10.2 RMS	kHz <u>max. Unit</u> +85 °C +90 °C g 15 ±15.75 V mA 5-1 (Pin 1 - 6 to Pin 7 – 9) mm mm 600 V 1020 V
f <u>General data</u> ¹⁾ T _A T _S m V _C I _C Sclear Screep V _{Sys}	Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage Current consumption Constructed and manufactored and teste Reinforced insulation, Insulation materia clearance (component without solder pad) creepage (component without solder pad) System voltage overvoltage category 3	DC200 min. typ. -40 -40 -40 13.5 ±11.4 ±12 or ± 18,5 ed in accordance with EN 61800- I group 1, Pollution degree 2 10.2 10.2 RMS	kHz <u>max. Unit</u> +85 °C +90 °C g 15 ±15.75 V mA 5-1 (Pin 1 - 6 to Pin 7 – 9) mm mm 600 V
f <u>Seneral data</u> ¹⁾ T _A T _S m V _C I _C Sclear Screep V _{Sys} V _{work} UPD	 Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage Current consumption Constructed and manufactored and tester Reinforced insulation, Insulation materia clearance (component without solder pad) creepage (component without solder pad) System voltage overvoltage category 3 Working voltage Working voltage 	DC200 min. typ. -40 -40 13.5 ±11.4 ±12 or ± 18,5 ed in accordance with EN 61800- I group 1, Pollution degree 2 10.2 10.2 RMS 800-5-1) RMS peak value	kHz max. Unit +85 °C +90 °C g 15 ±15.75 V mA 5-1 (Pin 1 - 6 to Pin 7 – 9) mm 600 V 1020 V 1400 V
f <u>Seneral data</u> ¹⁾ T _A T _S m V _C I _C Sclear Screep V _{Sys} V _{work} UPD	Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage Current consumption Constructed and manufactored and teste Reinforced insulation, Insulation materia clearance (component without solder pad) creepage (component without solder pad) System voltage voervoltage category 3 Working voltage (table 7 acc. to EN61	DC200 min. typ. -40 -40 -40 13.5 ±11.4 ±12 or ± 18,5 ed in accordance with EN 61800- I group 1, Pollution degree 2 10.2 10.2 RMS 800-5-1) RMS	kHz <u>max. Unit</u> +85 °C +90 °C g 15 ±15.75 V mA 5-1 (Pin 1 - 6 to Pin 7 – 9) mm mm 600 V 1020 V
f <u>Seneral data</u> ¹⁾ T _A T _S m V _C I _C Sclear Screep V _{Sys} V _{work} UPD	 Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage Current consumption Constructed and manufactored and tester Reinforced insulation, Insulation materia clearance (component without solder pad) creepage (component without solder pad) System voltage overvoltage category 3 Working voltage Working voltage 	DC200 min. typ. -40 -40 13.5 ±11.4 ±12 or ± 18,5 ed in accordance with EN 61800- I group 1, Pollution degree 2 10.2 10.2 RMS 800-5-1) RMS peak value	kHz max. Unit +85 °C +90 °C g 15 ±15.75 V mA 5-1 (Pin 1 - 6 to Pin 7 – 9) mm 600 V 1020 V 1400 V
f <u>Aeneral data</u> ¹⁾ TA TS M VC IC Sclear Screep Vsys Vwork UPD Max. potential d	Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage Current consumption Constructed and manufactored and teste Reinforced insulation, Insulation materia clearance (component without solder pad) creepage (component without solder pad) System voltage itference acc. to UL 508 suue Amendment	DC200 min. typ. -40 -40 13.5 ±11.4 ±12 or ± 18,5 ed in accordance with EN 61800- I group 1, Pollution degree 2 10.2 10.2 10.2 10.2 RMS 800-5-1) RMS peak value RMS	kHz max. Unit +85 °C +90 °C g 15 ±15.75 V mA 5-1 (Pin 1 - 6 to Pin 7 – 9) mm 600 V 1020 V 1400 V 600 V _{AC}
f Aeneral data ¹⁾ TA TS M VC IC Sclear Screep Vsys Vwork UPD Max. potential d Max. potential d	Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage Current consumption Constructed and manufactored and teste Reinforced insulation, Insulation materia clearance (component without solder pad) creepage (component without solder pad) System voltage Working voltage ifference acc. to UL 508	DC200 min. typ. -40 -40 13.5 ±11.4 ±12 or ± 18,5 ed in accordance with EN 61800- I group 1, Pollution degree 2 10.2 10.2 10.2 10.2 RMS 800-5-1) RMS peak value RMS	kHz max. Unit +85 °C +90 °C g 15 15 ±15.75 V MA 5-1 (Pin 1 - 6 to Pin 7 – 9) 600 V 1020 V 600 V AC
f <u>Aeneral data</u> ¹⁾ TA TS M VC IC Sclear Screep Vsys Vwork UPD Max. potential d	Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage Current consumption Constructed and manufactored and teste Reinforced insulation, Insulation materia clearance (component without solder pad) creepage (component without solder pad) System voltage overvoltage category 3 Working voltage (table 7 acc. to EN61 Rated discharge voltage ifference acc. to UL 508	DC200 min. typ. -40 -40 13.5 ±11.4 ±12 or ± 18,5 ed in accordance with EN 61800- I group 1, Pollution degree 2 10.2 10.2 10.2 10.2 RMS 800-5-1) RMS peak value RMS	kHz max. Unit +85 °C +90 °C g 15 15 ±15.75 V MA 5-1 (Pin 1 - 6 to Pin 7 – 9) 600 V 1020 V 600 V AC



K-No.: 24616	SPECIFICATION Item no			.: T60404-N4646-X410				
	For the electronic r DC, AC, pulsed, m Isolation between t	50 A Current Sensor For the electronic measurement of currents: DC, AC, pulsed, mixed, with a galvanic Isolation between the primary circuit (high power) and the secondary circuit (electronic circuit)				Date: 20.01.2022		
Customer: Star	ndard type	Custo	omers Part no.:		Page	3 of 5		
lectrical Data (in	vestigate by a type c	hecking)						
	reeligate by a type o	<u>neoking/</u>	min.	typ.	max.	Unit		
V _{Ctot}	Maximum supply ±15.75 ±18 V:1	voltage (without functio or 1s per hour	n)		±18	V		
Rs		sistance @ $T_A=85^{\circ}C$			88	Ω		
Rp	•	ance per turn @ $T_A=2$	25°C		0.36	mΩ		
Хті		of X @ $T_A = -40 \dots +8$			0.1	%		
loges	Offset current (inc	-			0.15	mA		
l _{ot}	Long term drift Off	• • • •		0.05		mA		
Іот	•	perature drift $I_0 @ T_A$	= -40+85°C	0.05		mA		
Іон		@ I _P =0 (caused by prin		0.04	0.1	mA		
$\Delta I_0 / \Delta V_C$	Supply voltage rej		.,		0.01	mA/V		
İoss	Offset ripple* (with	1 MHz- filter first ord	er)		0,15	mA		
loss	Offset ripple* (with	100 kHz- filter first c	order)	0.03	0.05	mA		
loss		20 kHz- filter first or coupling capacity (p	,	0.007	0.01	mA		
		0 Hz, 1 min/Oktave, ate of on/off – switching of t rocess of the sensor.			10g			
	An exceptionally high ra	ate of on/off - switching of t			J			
spection (Measu	An exceptionally high ra accelerates the aging p	ate of on/off – switching of t rocess of the sensor.	he supply voltage	e)				
`	An exceptionally high ra accelerates the aging p	ate of on/off – switching of t rocess of the sensor.	the supply voltage s at room temperatur	•		0+05 %		
$K_N(N_1/N_2)$ (V)	An exceptionally high ra accelerates the aging p urement after temperature M3011/6	ate of on/off – switching of the sensor.	he supply voltage	•	13 : 100	0±0.5 % mA		
K _N (N ₁ /N ₂) (V) I ₀ (V)	An exceptionally high ra accelerates the aging p urement after temperature M3011/6 M3226	ate of on/off – switching of the sensor.	the supply voltage s at room temperatur ttio (IP=3*10A, 40-8	•	13 : 100 < 0.1	mA		
K _N (N ₁ /N ₂) (V) I ₀ (V) V _{P,eff} (V)	An exceptionally high ra accelerates the aging p urement after temperature M3011/6 M3226 M3014	the of on/off – switching of the sensor.	the supply voltage s at room temperatur ttio (IP=3*10A, 40-8	30 Hz)	13 : 100 < 0.1 2.5			
K _N (N1/N2) (V) Io (V) VP,eff (V)	An exceptionally high ra accelerates the aging p urement after temperature M3011/6 M3226 M3014	the of on/off – switching of the sensor.	the supply voltage s at room temperatur ttio (IP=3*10A, 40-8 , 1s	30 Hz)	13 : 100 < 0.1	mA		
K _N (N ₁ /N ₂) (V) I ₀ (V) V _{P,eff} (V) V _e (AQL 1/S4	An exceptionally high ra accelerates the aging p urement after temperature M3011/6 M3226 M3014	te of on/off – switching of t rocess of the sensor.	the supply voltage s at room temperatur ttio (IP=3*10A, 40-8	30 Hz)	13 : 100 < 0.1 2.5 1500	mA kV V		
K _N (N1/N2) (V) Io (V) VP,eff (V) Ve (AQL 1/S4)	An exceptionally high ra accelerates the aging p urement after temperature M3011/6 M3226 M3014	the of on/off – switching of the rocess of the sensor.	s at room temperatur tio (IP=3*10A, 40-8 , 1s voltage acc. M3024	30 Hz)	13 : 100 < 0.1 2.5 1500	mA kV V		
KN(N1/N2) (V) Io (V) VP,eff (V) Ve (AQL 1/S4	An exceptionally high ra accelerates the aging p urement after temperature M3011/6 M3226 M3014 4) 1 - 6 to Pin 7 – 9) ing standard EN 61800	the of on/off – switching of the rocess of the sensor. Transformation ran Offset current Test voltage, rms Pin 1 - 6 to Pin 7 - 9 Partial discharge with Vvor (RMS) With insulation mater according (to M3064)	the supply voltage s at room temperatur ttio (IP=3*10A, 40-8 , 1s voltage acc. M302- erial group 1	30 Hz)	13 : 100 < 0.1 2.5 1500	mA kV V		
K _N (N1/N2) (V) Io (V) VP,eff (V) Ve (AQL 1/S4) vpe Testing (Pin Designed accord (Pin)	An exceptionally high ra accelerates the aging p urement after temperature M3011/6 M3226 M3014 4) 1 - 6 to Pin 7 – 9) ing standard EN 61800 HV transient test a (1,2 µs / 50 µs-wa Testing voltage ac	ate of on/off – switching of the rocess of the sensor. Transformation range of the samples of the sensor of the samples of th	s at room temperatur tio (IP=3*10A, 40-8 , 1s voltage acc. M3024	30 Hz)	13 : 100 < 0.1 2.5 1500 1875	mA kV V V		
K _N (N ₁ /N ₂) (V) Io (V) V _{P,eff} (V) V _e (AQL 1/S4)	An exceptionally high ra accelerates the aging p urement after temperature M3011/6 M3226 M3014	te of on/off – switching of t rocess of the sensor.	the supply voltage s at room temperatur ttio (IP=3*10A, 40-8	30 Hz)	13 : 100 < 0.1 2.5 1500	mA kV V		



	AELZE	SPECIFI	CATION		Item no.:	T60404-N4646-X410
K-No.: 2	4616	DC, AC, pulsed, Isolation betwee	c measurement of curr mixed, with a galva n the primary circuit d the secondary circuit	nic		Date: 20.01.2022
Customer	: Stand	ard type	Cı	stomers Part	no.:	Page 5 of 5
Explanatio	n of seve	er al of the terms	used in the tablets	(in alphabetica	<u>ll order)</u>	
I _{0Н} :	Zero var	iation of I_0 after ov	verloading with a DC	of tenfold the ra	ated value ($R_M = R_M$	MN)
lot:	Long ter	m drift of I ₀ after 1	00 temperature cycl	es in the range	40 bis 85 °C.	
tr:	Respons at I _P = 0	se time (describe t ,9 · I _{Pmax} between	he dynamic perform a rectangular curre	ance for the spe nt and the outpu	cified measurement t current.	nt range), measured as delay time
∆t (I _{Pmax}):			ynamic performance nd the output curren			g short circuit current) ₁ /dt = 100 A/μs.
X _{ges} (I _{PN}):			rors over the temper	ature range by r	neasuring a curren	t IPN:
	$X_{ges} = 1$	$00 \cdot \left \frac{\mathbf{I}_{s} \left(\mathbf{I}_{PN} \right)}{\mathbf{K}_{N} \cdot \mathbf{I}_{PN}} - \right $	%			
X:	Permiss	ible measurement	error in the final ins	pection at RT, d	efined by	
	X =10	$10 \cdot \left \frac{I_{SB}}{I_{SN}} - 1 \right \%$				
	where Is	$_{\rm B}$ is the output DC	value of an input D	C current of the	same magnitude a	s the (positive) rated current ($I_0 = 0$
X _{Ti} :	Tempera obtained		ted value orientated	output term. Isn	(cf. Notes on F _i) ir	n a specified temperature range,
	$X_{\mathrm{Ti}} =$	$100 \cdot \left \frac{\mathrm{I}_{\mathrm{SB}}(\mathrm{T}_{\mathrm{A2}})}{\mathrm{I}_{\mathrm{SB}}(\mathrm{T}_{\mathrm{A2}})} \right $	$\frac{-I_{SB}(T_{A1})}{I_{SN}} \%$			
EL:	Linearity	r fault defined by	$\varepsilon_{\rm L} = 100 \cdot \left \frac{I_{\rm P}}{I_{\rm PN}} \right $	$-\frac{I_{Sx}}{V}$		
W			$\mid I_{PN}$ Isx the correspondin		$_{\text{IN}}$: see notes of F_{i} ($I_{0} = 0$).
	_	T			T	
Hrsg.: KB-E	=	Bearb: Le		B-PM IA: KRe.		freig.: SB released